Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5138	156/345;216/54,63,67,71;438/712. 734;257/187,213;427/569,579,534. ccls.	US-PGPUB; USPAT	OR	OFF	2006/02/03 16:23
L2	126691	Semiconductor adj device	US-PGPUB; USPAT	OR	OFF	2006/02/03 16:23
L3	75167	L2 and etch\$4	US-PGPUB; USPAT	OR	OFF	2006/02/03 16:23
L4	3414	L3 and high adj aspect adj ratio	US-PGPUB; USPAT	OR	OFF	2006/02/03 16:23
L5	623	L4 and (RF or radio adj frequency) adj power	US-PGPUB; USPAT	OR	OFF	2006/02/03 16:23
L6	45	L5 and etch\$4 adj dielectric adj layer	US-PGPUB; USPAT	OR	OFF	2006/02/03 16:23
L7	7	L1 and L6	US-PGPUB; USPAT	OR	OFF	2006/02/03 16:24
S1	124652	Semiconductor adj device	US-PGPUB; USPAT	OR	OFF	2005/12/27 10:00
S2	73913	S1 and etch\$4	US-PGPUB; USPAT	OR	OFF	2005/12/23 15:00
S3	3362	S2 and high adj aspect adj ratio	US-PGPUB; USPAT	OR	OFF	2005/12/23 15:00
S4	620	S3 and (RF or radio adj frequency) adj power	US-PGPUB; USPAT	OR	OFF	2005/12/23 15:01
S5	6	S4 and (first or second) adj frequency	US-PGPUB; USPAT	OR	OFF	2005/12/23 15:01
S6	45	S4 and etch\$4 adj dielectric adj layer	US-PGPUB; USPAT	OR	OFF	2005/12/27 08:48
<b>S7</b>	3	S6 and etch adj gas	US-PGPUB; USPAT	OR	OFF	2005/12/23 15:26
S8	1	("6743727").PN.	USPAT; USOCR	OR	OFF	2005/12/23 16:26
S9	0	("2004/0221958").URPN.	USPAT	OR	OFF	2005/12/27 08:46
S10	124785	Semiconductor adj device	US-PGPUB; USPAT	OR	OFF	2005/12/27 08:48
S11	73993	S10 and etch\$4	US-PGPUB; USPAT	OR	OFF	2005/12/27 08:48
S12	3367	S11 and high adj aspect adj ratio	US-PGPUB; USPAT	OR	OFF	2005/12/27 08:48
S13	620	S12 and (RF or radio adj frequency) adj power	US-PGPUB; USPAT	OR	OFF	2005/12/27 08:48
S14	0	S13 and etch\$4 adj dielectric adj layer	EPO; JPO; DERWENT	OR	OFF	2005/12/27 08:48
S15	1	("6500314").PN.	USPAT; USOCR	OR	OFF	2005/12/27 10:01

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C:\Documents and Settings\mangadi\My Documents\EAST\Workspaces\High Aspect Ratio etch using RF power.wsp

S16	1	("6436253").PN.	USPAT; USOCR	OR	OFF	2005/12/27 10:16
S17	1	("4464223").PN.	USPAT; USOCR	OR	OFF	2005/12/27 10:16
S18	8	(("5626716") or ("5656123") or ("5716485") or ("6127278") or ("6303510") or ("6387287") or ("6433297") or ("6506674")).PN.	USPAT; USOCR	OR	OFF	2005/12/27 10:36
S19	124785	Semiconductor adj device	US-PGPUB; USPAT	OR	OFF	2005/12/28 08:54
S20	73993	S19 and etch\$4	US-PGPUB; USPAT	OR	OFF	2005/12/28 08:54
S21	3367	S20 and high adj aspect adj ratio	US-PGPUB; USPAT	OR	OFF	2005/12/28 08:54
S22	620	S21 and (RF or radio adj frequency) adj power	US-PGPUB; USPAT	OR	OFF	2005/12/28 08:54
S23	6	S22 and (first or second) adj frequency	US-PGPUB; USPAT	OR	OFF	2005/12/28 08:54
S24	45	S22 and etch\$4 adj dielectric adj layer	US-PGPUB; USPAT	OR	OFF	2005/12/28 08:54
S25	3	S24 and etch adj gas	US-PGPUB; USPAT	OR	OFF	2005/12/28 08:54
S26	1	("6743727").PN.	USPAT; USOCR	OR	OFF	2005/12/28 08:54
S27	0	("2004/0221958").URPN.	USPAT	OR	OFF	2005/12/28 08:54
S28	124785	Semiconductor adj device	US-PGPUB; USPAT	OR	OFF	2005/12/28 08:54
S29	73993	S28 and etch\$4	US-PGPUB; USPAT	OR	OFF	2005/12/28 08:54
S30	3367	S29 and high adj aspect adj ratio	US-PGPUB; USPAT	OR	OFF	2005/12/28 08:54
S31	620	S30 and (RF or radio adj frequency) adj power	US-PGPUB; USPAT	OR	OFF	2005/12/28 08:54
S32	0	S31 and etch\$4 adj dielectric adj layer	EPO; JPO; DERWENT	OR	OFF	2005/12/28 08:54
S33	1	("6500314").PN.	USPAT; USOCR	OR	OFF	2005/12/28 08:54
S34	1	("6436253").PN.	USPAT; USOCR	OR	OFF	2005/12/28 08:54
S35	1	("4464223").PN.	USPAT; USOCR	OR	OFF	2005/12/28 08:54
S36	8	(("5626716") or ("5656123") or ("5716485") or ("6127278") or ("6303510") or ("6387287") or ("6433297") or ("6506674")).PN.	USPAT; USOCR	OR	OFF	2005/12/28 08:54

S37	1	("6942816").PN.	USPAT; USOCR	OR	OFF	2005/12/28 08:59
S38	4	(("6824627") or ("6942816") or ("6872281") or ("6391787")).PN.	USPAT; USOCR	OR	OFF	2005/12/28 09:14
S39	2622	156/345;216/54,63,67,71;438/712. 734.ccls.	US-PGPUB; USPAT	OR	OFF	2006/02/03 16:11
S40	3	S24 and S39	US-PGPUB; USPAT	OR	OFF	2005/12/28 09:17